

» Applications

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

» Product Summary

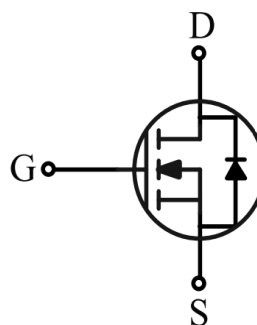
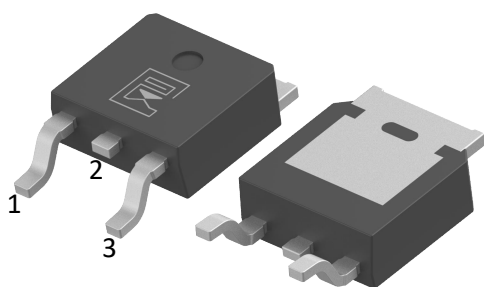
V_{DS}	500	V
I_D	9	A
$R_{DS(ON)},_{Typ@10V}$	0.66	Ω
Q_g	30	nC

» Features

- Low $R_{DS(ON)}$
- Ultra Low Gate Charge
- 100% UIS and RG Tested



TO-252



Gate: 1
 Drain: 2
 Source: 3

» Package Marking and Ordering Information

Ordering code	Marking	Package	Packaging	Min. package quantity
MKIRF9N50	MKIRF9N50	TO-252	Tape & Reel	3000

» Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current (Note 1)	I_D	9	A
Drain Current-Pulsed (Note 1)	I_{DM}	36	A
Total Dissipation	P_D	145	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55-150	°C
Single Pulse Avalanche Energy (Note 2)	E_{AS}	360	mJ

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

» Thermal Characteristics

Parameter	Symbol	Max	Unit
Maximum Junction-to-Case	$R_{\theta JC}$	0.86	°C/W
Maximum Junction-to-Ambient	$R_{\theta JA}$	60	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD}=50V$, $T_{ch}=25^{\circ}C$ (initial), $I_{AS}=9A$, $R_g=25\Omega$.

Note 3: The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}C$. The value in any given application depends on the user's specific board design.

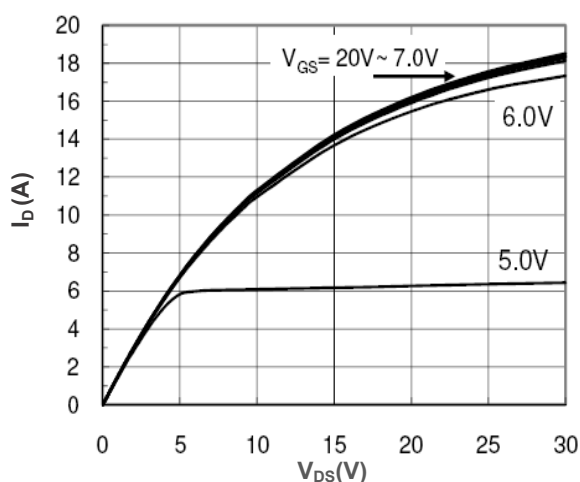
Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Electrical Characteristics (Tc=25°C unless otherwise noted)

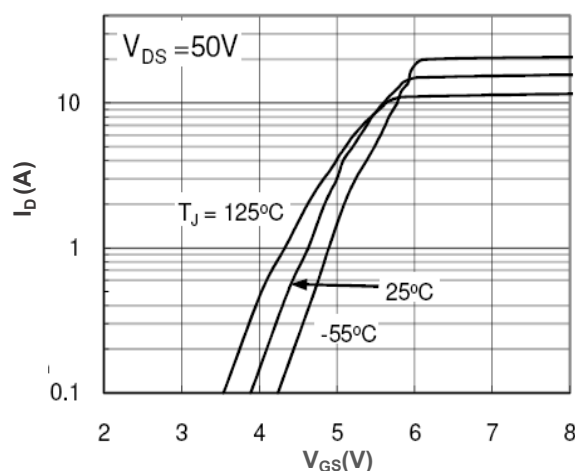
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	500	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =500V,V _{GS} =0V	-	-	1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±30V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} ,I _D =250uA	2.0	3.0	4.0	V
Drain-Source On Resistance	R _{DS(ON)}	V _{GS} =10V,I _D =4.5A	-	0.66	0.85	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V, f=1.0MHz	-	1020	-	pF
Output Capacitance	C _{oss}		-	120	-	pF
Reverse Transfer Capacitance	C _{rss}		-	10	-	pF
Gate Resistance	R _g	V _{DS} =0V,V _{GS} =0V, f=1.0MHz	-	1.6	-	Ω
Switching Paramters						
Turn-On Delay Time	t _{d(on)}	V _{DS} =250V,I _D =9A, V _{GS} =10V,R _G =25Ω	-	11	-	ns
Turn-On Rise Time	t _r		-	23	-	ns
Turn-Off Delay Time	t _{d(off)}		-	26	-	ns
Turn-Off Rise Time	t _f		-	19	-	ns
Total Gate Charge	Q _g	V _{DS} =400V,I _D =9A, V _{GS} =10V	-	30	-	nC
Gate-Source Charge	Q _{gs}		-	4	-	nC
Gate-Drain Charge	Q _{gd}		-	15	-	nC
Source-Drain Characteristics						
Max. Diode Forward Cuurent	I _S		-	-	9	A
Max. Pulsed Forward Cuurent	I _{SM}		-	-	36	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =9A	-	0.86	1.5	V
Reverse Recovery Time	t _{rr}	V _R =400V,I _F =9A, di/dt=100A/us	-	360	-	ns
Reverse Recovery Charge	Q _{rr}		-	4	-	μC



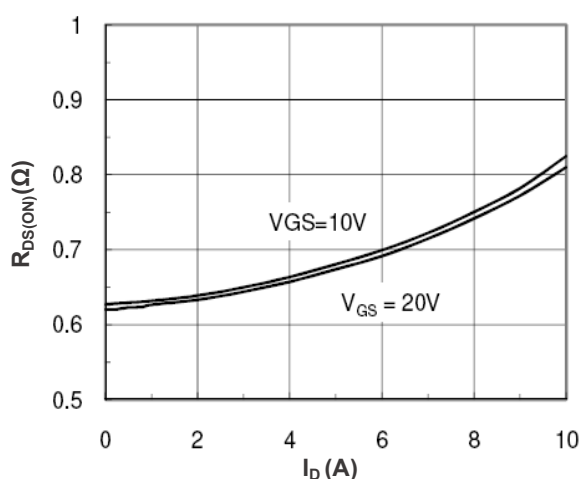
Characteristics Curves



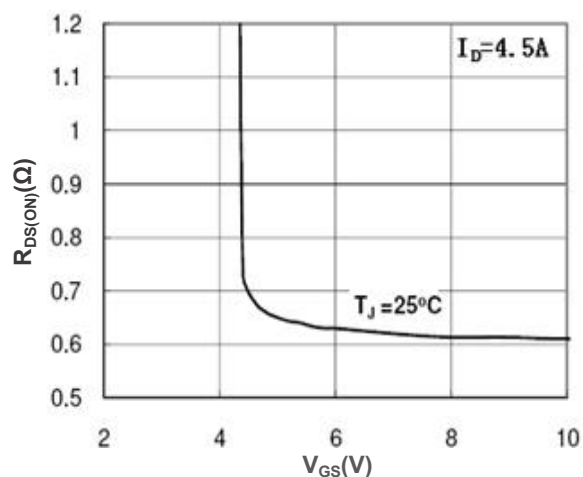
Output Characteristics



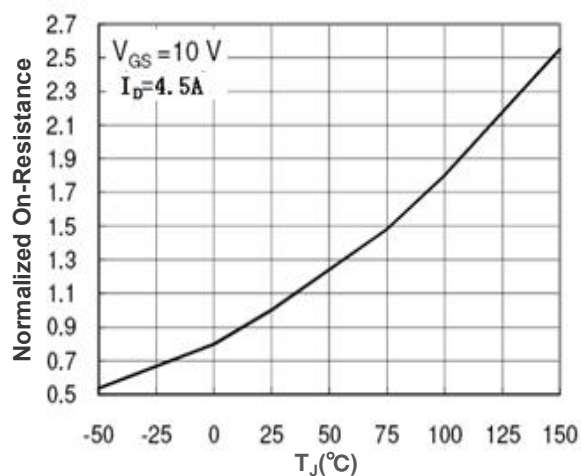
Transfer Characteristics



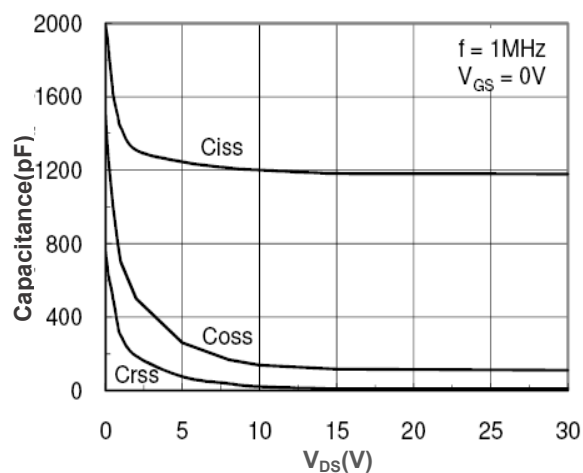
On Resistance Vs Drain Current



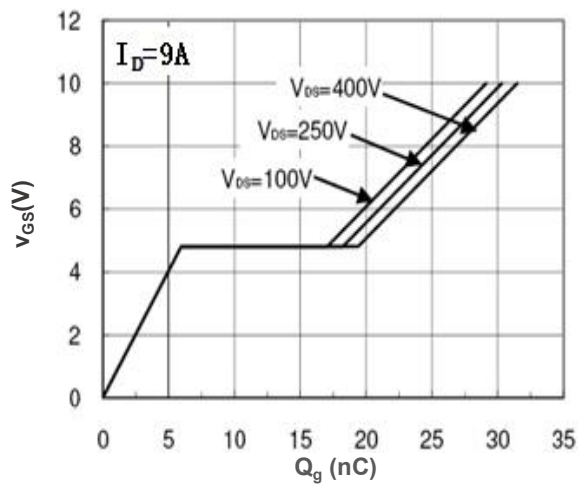
On Resistance Vs Gate Source Voltage



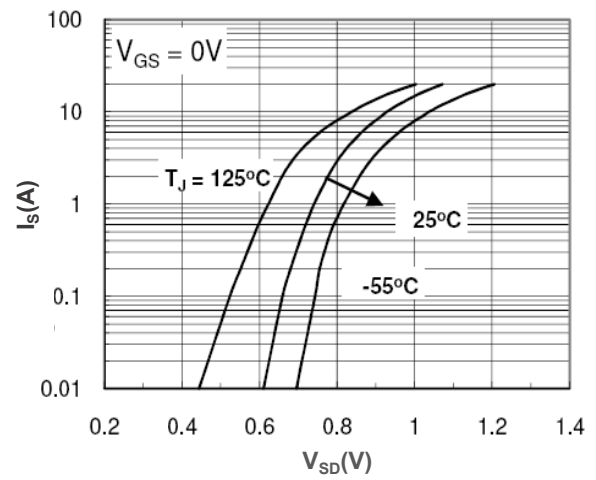
Rdson-JunctionTemperature



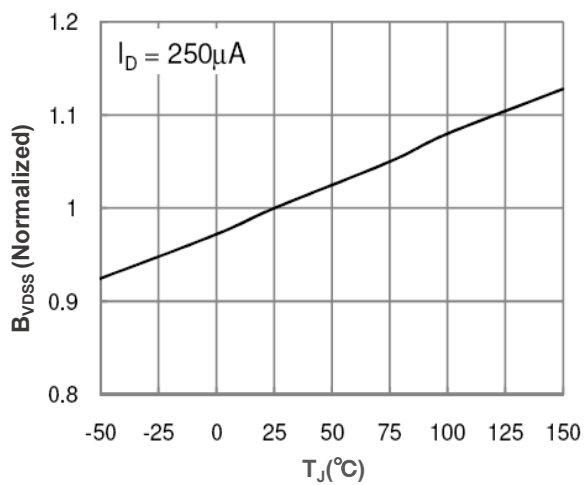
Capacitance



Gate Charge Waveform



Source-Drain Diode Forward Voltage



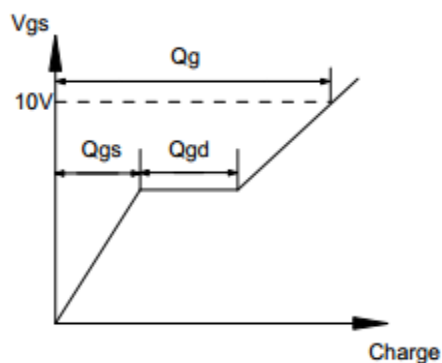
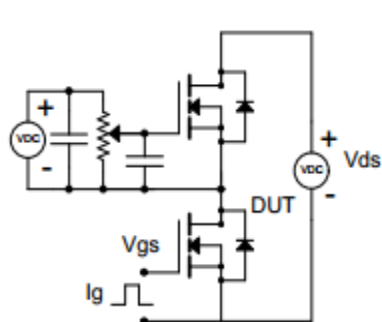
Breakdown Voltage Vs Junction Temperature

Note : The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

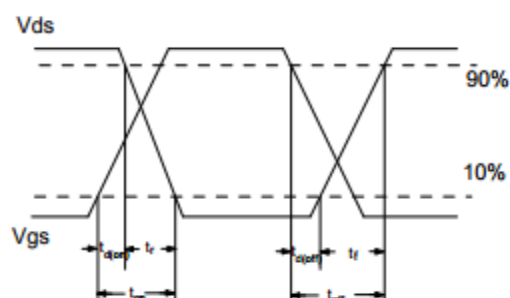
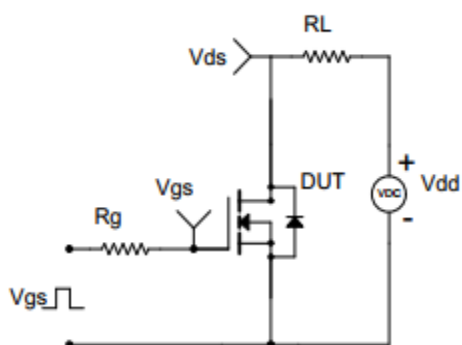


Test Circuit & Waveform

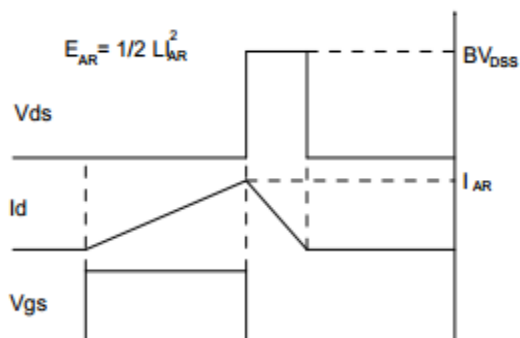
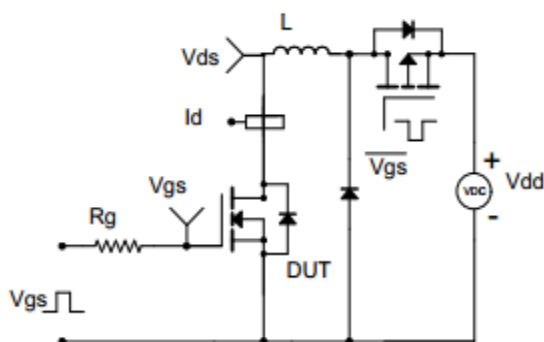
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveform





TO-252 Package Dimensions

Unit: mm

Symbol	Min	Nom	Max	Symbol	Min	Nom	Max
A	2.20		2.40	L	9.80		10.40
A1	0.00		0.13	L1		2.90	
b	0.66		0.86	L2	1.40		1.60
c	0.46		0.58	L3		1.80	
D	6.50		6.70	L4	0.60		1.00
D1	5.10		5.46	L5	0.90		1.25
D2		4.83		Φ	1.1		1.30
E	6.00		6.20	θ	0°		8°
e	2.19		2.39	V		5.35	

